

## 1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO-220 plastic package.

## 2. Features and benefits

- Trench structure
- High junction temperature up to 150°C
- High efficiency
- Low forward voltage drop, negligible switching losses

## 3. Applications

- DC to DC converters
- Freewheeling diode
- OR-ing diode

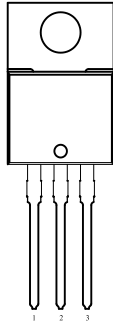
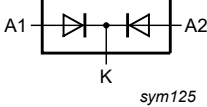
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	100	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; $T_{mb} \leq 133$ °C; square-wave pulse; per diode; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	20	A
$I_{O(AV)}$	average output current	$\delta = 0.5$ ; $T_{mb} \leq 130$ °C; square-wave pulse; both diodes conducting	-	-	40	A
<b>Static characteristics</b>						
$V_F$	forward voltage	$I_F = 10$ A; $T_j = 25$ °C; <a href="#">Fig. 6</a> ; per diode	-	0.53	0.59	V
		$I_F = 10$ A; $T_j = 125$ °C; <a href="#">Fig. 6</a> ; per diode	-	0.49	0.56	V
		$I_F = 20$ A; $T_j = 25$ °C; <a href="#">Fig. 6</a> ; per diode	-	0.64	0.71	V
		$I_F = 20$ A; $T_j = 125$ °C; <a href="#">Fig. 6</a> ; per diode	-	0.61	0.68	V
$I_R$	reverse current	$V_R = 100$ V; $T_j = 25$ °C; <a href="#">Fig. 7</a> ; <a href="#">Fig. 8</a> ; per diode	-	-	50	$\mu$ A
		$V_R = 100$ V; $T_j = 125$ °C; <a href="#">Fig. 7</a> ; <a href="#">Fig. 8</a> ; per diode	-	-	30	mA

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	 <p style="text-align: center;"><b>TO-220E</b></p>	
2	K	cathode		
3	A2	anode 2		
mb	K	mounting base; connected to cathode		

## 6. Ordering information

Table 3. Ordering information

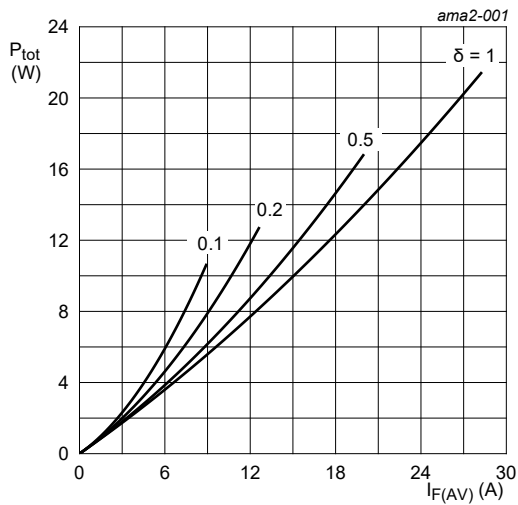
Type number	Package		Version
	Name	Description	
WNS40H100C	TO-220E	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	TO-220E

## 7. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

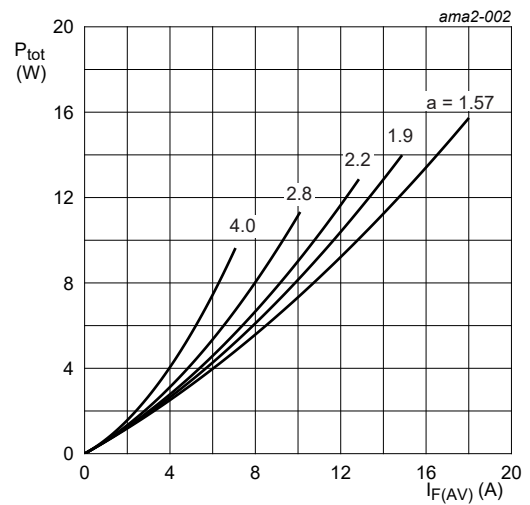
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	100	V
$V_{RWM}$	limiting crest working reverse voltage		-	100	V
$V_R$	limiting reverse voltage	DC	-	100	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; $T_{mb} \leq 133\text{ }^\circ\text{C}$ ; square-wave pulse; per diode; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	20	A
$I_{O(AV)}$	average output current	$\delta = 0.5$ ; $T_{mb} \leq 130\text{ }^\circ\text{C}$ ; square-wave pulse; both diodes conducting	-	40	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; sine-wave pulse; per diode; <a href="#">Fig. 4</a>	-	380	A
		$t_p = 8.3\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; sine-wave pulse; per diode	-	418	A
$T_{stg}$	storage temperature		-40	150	$^\circ\text{C}$
$T_j$	junction temperature		-	150	$^\circ\text{C}$



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 0.557\text{ V}; R_s = 0.0071\ \Omega$$

**Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode**



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

$$V_o = 0.570\text{ V}; R_s = 0.0071\ \Omega$$

**Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode**

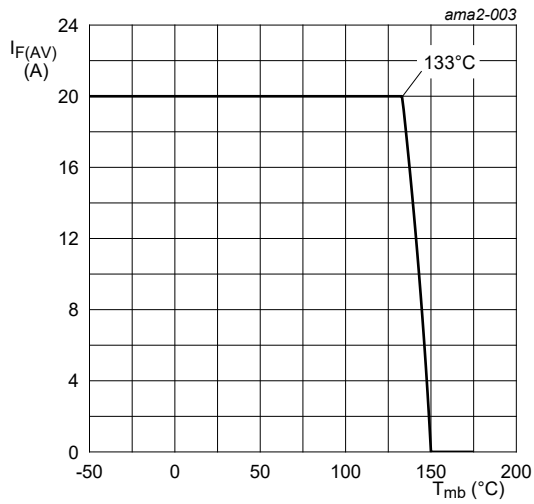


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

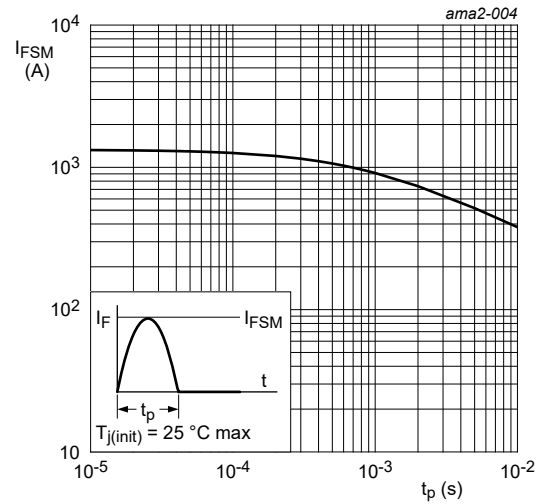


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

### 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	per diode; Fig. 5	-	-	1	K/W
		both diodes conducting	-	-	0.6	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

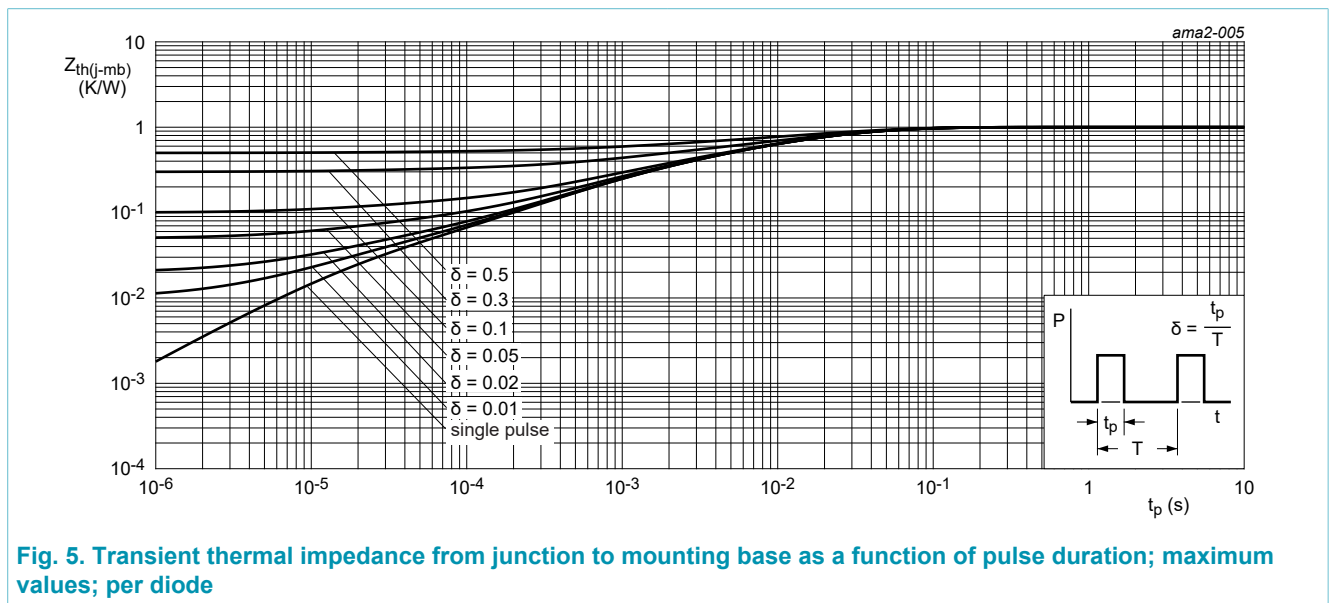
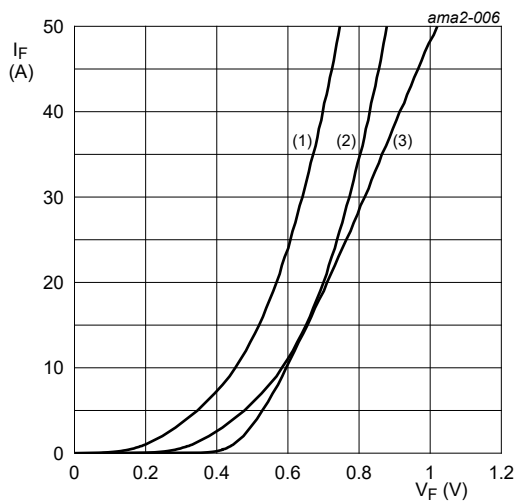


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

### 9. Characteristics

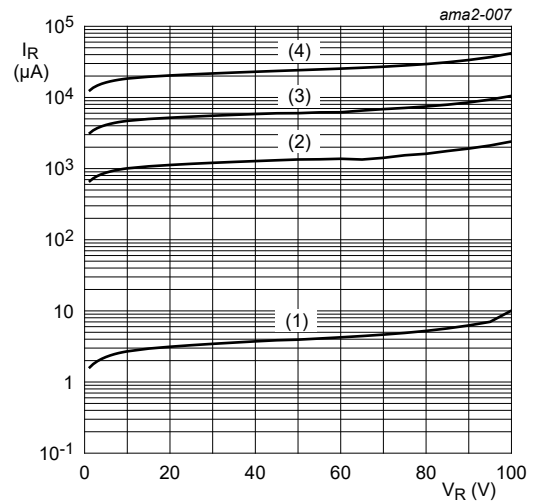
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_F$	forward voltage	$I_F = 10\text{ A}; T_j = 25\text{ °C};$ Fig. 6; per diode	-	0.53	0.59	V
		$I_F = 10\text{ A}; T_j = 125\text{ °C};$ Fig. 6; per diode	-	0.49	0.56	V
		$I_F = 20\text{ A}; T_j = 25\text{ °C};$ Fig. 6; per diode	-	0.64	0.71	V
		$I_F = 20\text{ A}; T_j = 125\text{ °C};$ Fig. 6; per diode	-	0.61	0.68	V
$I_R$	reverse current	$V_R = 100\text{ V}; T_j = 25\text{ °C};$ Fig. 7; Fig. 8; per diode	-	-	50	$\mu\text{A}$
		$V_R = 100\text{ V}; T_j = 125\text{ °C};$ Fig. 7; Fig. 8; per diode	-	-	30	mA



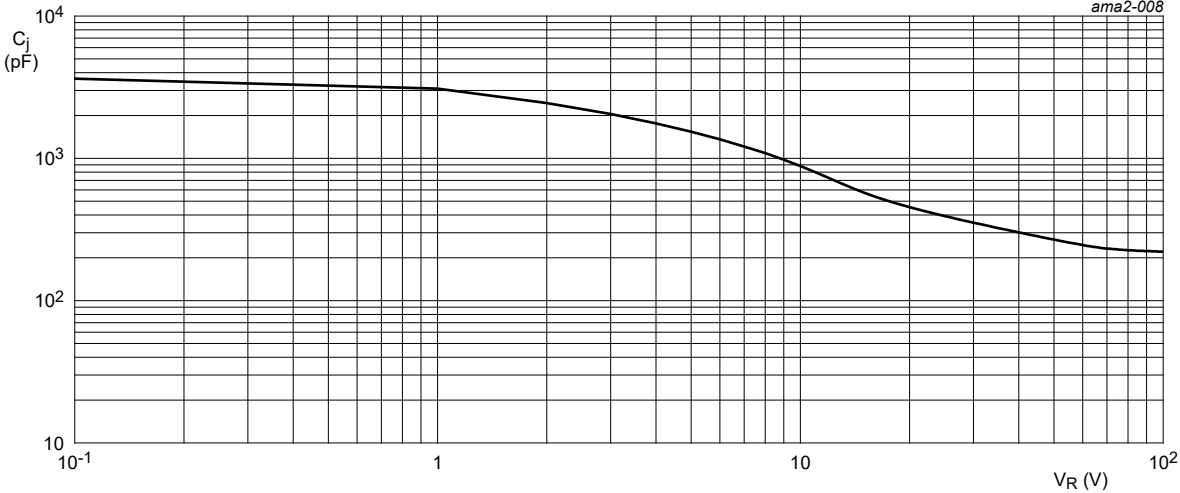
$V_o = 0.557\text{ V}; R_s = 0.0071\ \Omega$   
 (1)  $T_j = 150\text{ °C};$  typical values  
 (2)  $T_j = 150\text{ °C};$  maximum values  
 (3)  $T_j = 25\text{ °C};$  maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



(1)  $T_j = 25\text{ °C};$  typical values  
 (2)  $T_j = 100\text{ °C};$  typical values  
 (3)  $T_j = 125\text{ °C};$  typical values  
 (4)  $T_j = 150\text{ °C};$  typical values

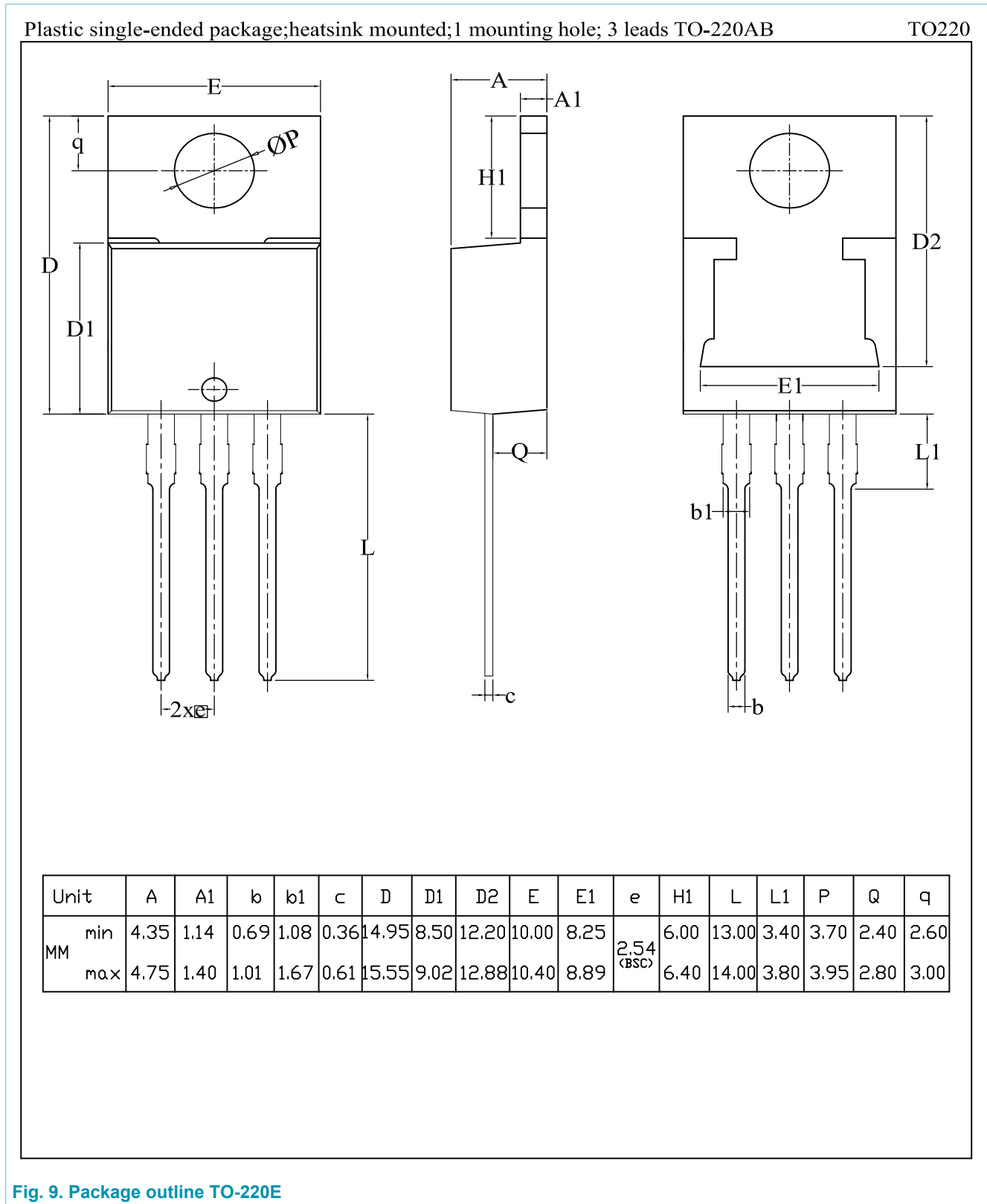
Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values



f = 1 MHz; Tj = 25 °C

Fig. 8. Junction capacitance as a function of applied reverse voltage; per diode; typical values

### 10. Package outline





## 11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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